

DIO1568

Low Power, Dual SIM Card Analog Switch

Features

- Switch type: SPDT (4X)
- Voltage operation: 1.65 V to 5.5 V
- Low on-resistance: 0.85 Ω at SIM path; 2.7 Ω at other paths
- 20 pF C_{ON} at DAT/CLK/RST path
- Low power consumption
- Packaged: 16-Lead QFN1.8*2.6 and 16-Lead QFN3*3

Descriptions

The DIO1568 is a quad single-pole, double-throw (SPDT) analog switch targeted at dual SIM card multiplexing. The DIO1568 operates from a single 1.65 V to 5.5 V supply and features an ultra-low on-resistance of 0.85 Ω at SIM path to ensure minimal voltage drop in other paths. This device is fabricated with sub-micron CMOS technology to achieve fast switching speeds and is designed for break-before-make operation.

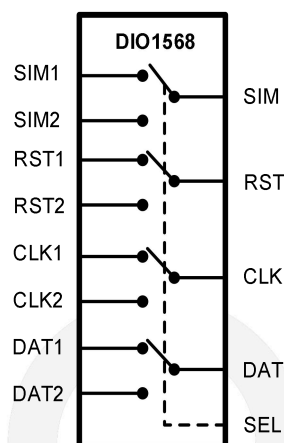
The DIO1568 features a very low quiescent current even when the control voltage is lower than the V_{CC} supply. This allows mobile handset applications direct interface with the baseband processor general-purpose I/Os.

The DIO1568 provides two Green packages: QFN1.8*2.6-16 and QFN3*3-16.

Applications

- Cell-Phones/PDAs
- Set-top boxes
- Digital cameras
- Notebooks
- TV/ LCD monitors

Block Diagram





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Low Power, Dual SIM Card Analog Switch

Ordering Information

Order Part Number	Top Marking	RoHS	T _A	Package	
DIO1568LN16	DE6H	Green	-40 to 85°C	QFN1.8*2.6-16	Tape & Reel, 3000
DIO1568CL16	DAE6H	Green	-40 to 85°C	QFN3*3-16	Tape & Reel, 5000

Pin Assignment

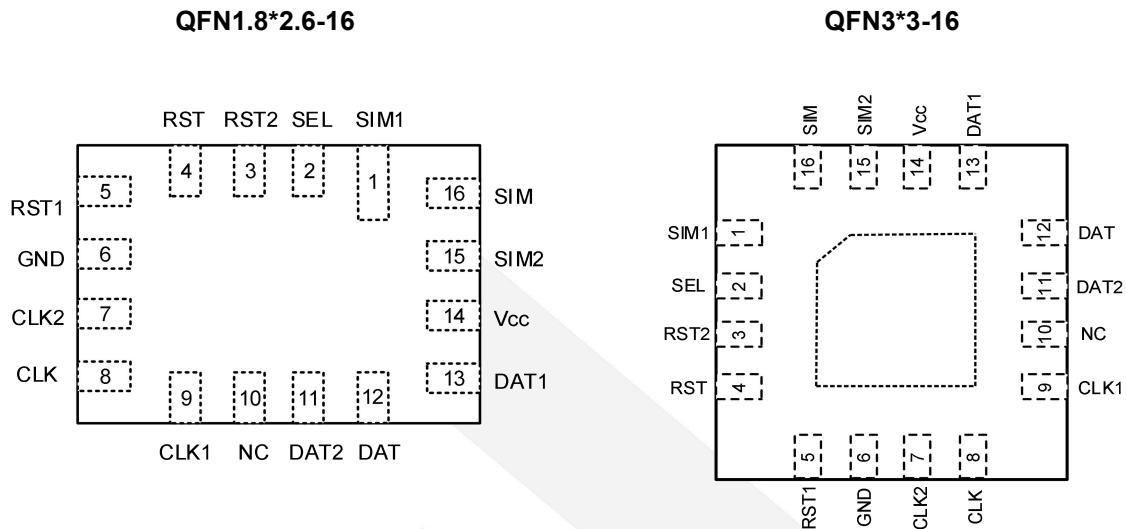


Figure 1 Top view

Pin Descriptions

Pin No.	Pin Name	Description
3, 4, 5, 7, 8, 9,	DATn, RSTn, CLKn	Data input
1, 15, 16	SIMn	SIM input
11, 12, 13,	SIM, DAT, CLK, RST	Common port
2	SEL	Select
6, 14	V _{CC} / GND	Power
10	NC	Not connected

Truth Table

SEL	Function
L	SIM = SIM1, DAT = DAT1, RST = RST1, CLK = CLK1
H	SIM = SIM2, DAT = DAT2, RST = RST2, CLK = CLK2

Absolute Maximum Ratings

Stresses beyond those listed under the Absolute Maximum Rating table may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other condition beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Symbol	Parameter	Min	Max	Unit
V_{CC}	Supply voltage	-0.5	6	V
V_S	Switch voltage	-0.5	$V_{CC} + 0.3$	V
V_{IN}	DC input I/O voltage	-0.5	V_{CC}	V
I_{IK}	DC input diode current	-50		mA
I_{OUT}	DC output current (DAT, CLK, RST, SIM)		400	mA
I_{Peak}	Peak current (pulsed at 1 ms, 10% duty cycle)		500	mA
P_D	Continuous power dissipation ($T_A = 85^{\circ}C$) (15.6 mW/ $^{\circ}C$ above $85^{\circ}C$)		1.25	W
T_{STG}	Storage temperature range	-65	150	$^{\circ}C$
T_J	Junction temperature		150	$^{\circ}C$
T_L	Lead temperature (soldering 10 s)		260	$^{\circ}C$

Recommend Operating Conditions

Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. DIOO does not recommend exceeding them or designing to absolute maximum ratings.

Symbol	Parameter	Min	Max	Unit
V_{CC}	Supply voltage	1.65	5.5	V
V_{IN}	Control input voltage (SEL)	0	V_{CC}	V
V_S	Switch I/O voltage	0	V_{CC}	V
I_{OUT}	DC output current (DAT, CLK, RST)		50	mA
I_{SIM}	DC output current (SIM)		150	mA
T_A	Operating temperature	-40	85	$^{\circ}C$

DC Electrical Characteristics

All typical value is at 25°C unless otherwise specified.

Symbol	Parameter	Conditions	V _{CC} (V)	Temp	Min	Typ	Max	Unit
V _{IH}	Input voltage high		1.65 to 4.5	-40 to 85°C	0.9			V
				25°C		0.8		V
V _{IL}	Input voltage low		1.65 to 4.5	-40 to 85°C			0.4	V
I _{IN}	Control input leakage	V _{SW} = 0 to V _{CC}	4.5	25°C	-1		1	uA
I _{NC(OFF)} I _{NO(OFF)}	Off leakage current	RSTn, DATn, CLKn, SIMn = 0.3 or 3.6 V	4.5	25°C	-1		1	uA
I _{NC(ON)} I _{NO(ON)}	ON leakage current	RSTn, DATn, CLKn, SIMn = 0.3 or 3.6 V	4.5	25°C	-1		1	uA
I _{CC}	Quiescent supply current	V _{IN} = 0 V or V _{CC} , I _{OUT} = 0 V	4.5	25°C		0.6	1	uA
R _{OND}	RST, DAT, CLK, resistance	I _{OUT} = -20 mA, V _{SW} = 2.3 V	2.7	-40 to 85°C		2.7		Ω
R _{ONS}	SIM resistance	I _{OUT} = -100 mA, V _{SW} = 2.3 V	2.7	-40 to 85°C		0.85		Ω
ΔR _{ON}	Delta on resistance	V _{SW} = 0V, I _{ON} = -20 mA	2.7	-40 to 85°C		0.2		Ω
R _{FLAT(ON)}	On resistance flatness	I _{OUT} = 100 mA, RSTn, CLKn, SIMn = 0 to V _{CC}	2.7	-40 to 85°C			0.8	Ω
I _{CCT}	Increase in I _{CC} current per control voltage and V _{CC}	V _{IN} = 0.8 V	4.5	25°C		1		μA
		V _{IN} = 1.5 V	4.5	25°C		0.61		μA

Capacitance

Symbol	Parameter	Conditions	Temp	Min	Typ	Max	Unit
C _{IN}	Control pin input capacitance		-40 to 85°C		2		pF
C _{OND}	DAT, CLK, RST on capacitance	f = 1 MHz	-40 to 85°C		20		pF
C _{ONS}	SIM on capacitance	f = 1 MHz	-40 to 85°C		100		pF
C _{OFFD}	DAT, CLK, RST off capacitance	f = 1 MHz	-40 to 85°C		5		pF
C _{OFFS}	SIM off capacitance	f = 1 MHz	-40 to 85°C		30		pF

AC Electrical Characteristics

All typical value are for $V_{CC} = 3.3\text{ V}$ at 25°C unless otherwise specified.

Symbol	Parameter	Conditions	$V_{CC}(\text{V})$	Temp	Min	Typ	Max	Unit
t_{OND}	Turn-on time (DAT, CLK, RST)	$R_L = 50\ \Omega$, $C_L = 35\text{ pF}$, $V_{\text{SW}} = 1.5\text{ V}$	2.7 to 3.6	$-40\text{ to }85^\circ\text{C}$		90		ns
t_{OFFD}	Turn-off time (DAT, CLK, RST)	$R_L = 50\ \Omega$, $C_L = 35\text{ pF}$, $V_{\text{SW}} = 1.5\text{ V}$	2.7 to 3.6	$-40\text{ to }85^\circ\text{C}$		60		ns
t_{ONS}	Turn-on time (SIM)	$R_L = 50\ \Omega$, $C_L = 35\text{ pF}$, $V_{\text{SW}} = 1.5\text{ V}$	2.7 to 3.6	$-40\text{ to }85^\circ\text{C}$		90		ns
t_{OFFS}	Turn-off time (SIM)	$R_L = 50\ \Omega$, $C_L = 35\text{ pF}$, $V_{\text{SW}} = 1.5\text{ V}$	2.7 to 3.6	$-40\text{ to }85^\circ\text{C}$		60		ns
t_{BBMD}	Break-before-make	$R_L = 50\ \Omega$, $C_L = 35\text{ pF}$, $V_{\text{SW}} = 1.5\text{ V}$	2.7 to 3.6	25°C		50		ns
t_{PD}	Propagation delay (DAT, CLK, RST)	$R_L = 50\ \Omega$, $C_L = 35\text{ pF}$	3.3	25°C			0.5	ns
OIRR	Off isolation (DAT, CLK, RST)	$R_L = 50\ \Omega$, $f = 10\text{ MHz}$	2.7 to 3.6	25°C		-50		dB
Xtalk	Non-adjacent channel crosstalk (DAT, CLK, RST)	$R_L = 50\ \Omega$, $f = 10\text{ MHz}$	2.7 to 3.6	25°C		-75		dB
BW	-3dB bandwidth (DAT, CLK, RST)	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$	2.7 to 3.6	25°C		200		MHz
	-3 dB bandwidth (SIM)	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$	2.7 to 3.6	25°C		60		MHz

Specifications subject to change without notice.

Typical Performance Characteristics

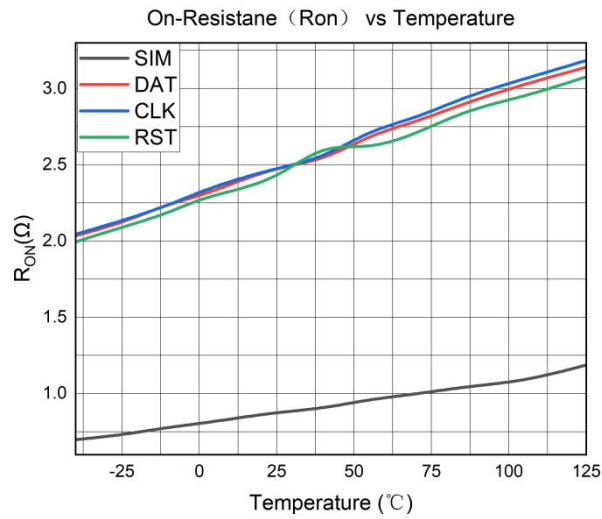

$$V_{CC} = 3.3 \text{ V}, V_{SW} = 2.3 \text{ V}$$

Figure 2. On-resistance (R_{ON}) vs Temperature

Test Diagrams

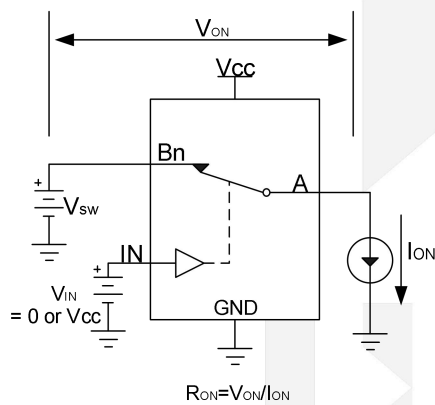


Figure 3. Switch-on resistor

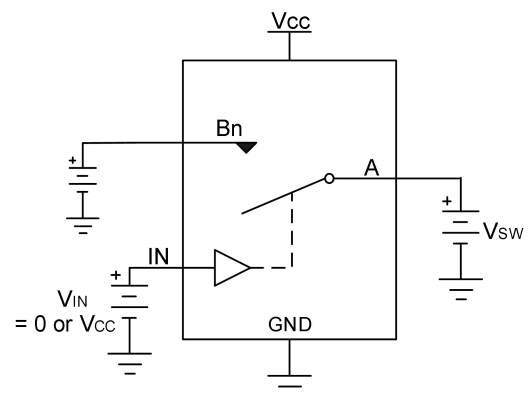


Figure 4. Switch-off leakage

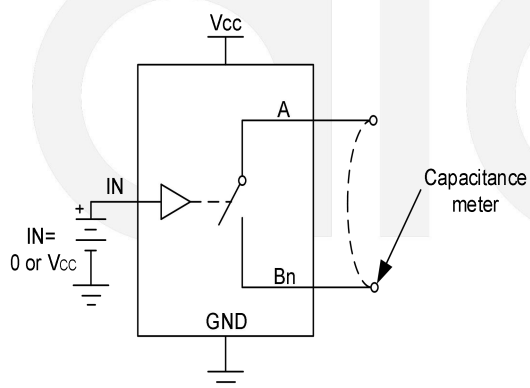


Figure 5. On/off capacitance test

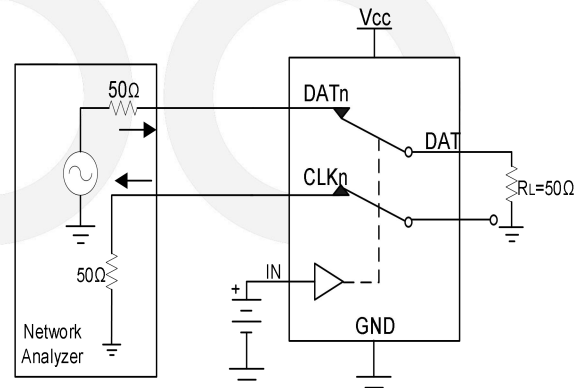


Figure 6. Channel-to-channel crosstalk

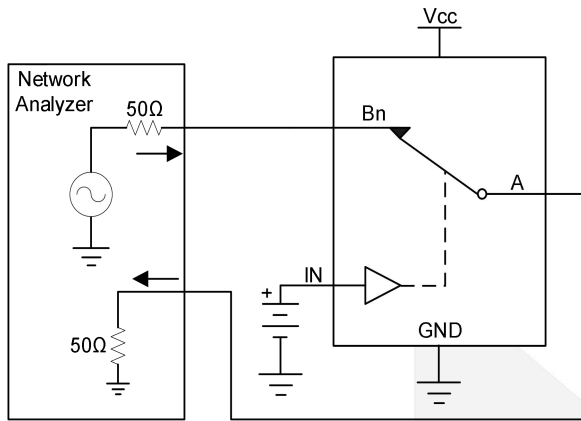


Figure 7. Bandwidth

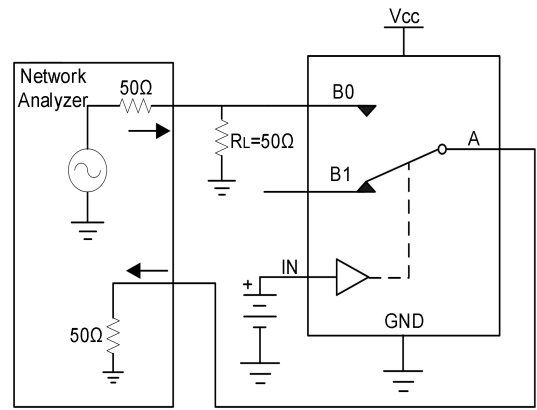


Figure 8. Off-isolation

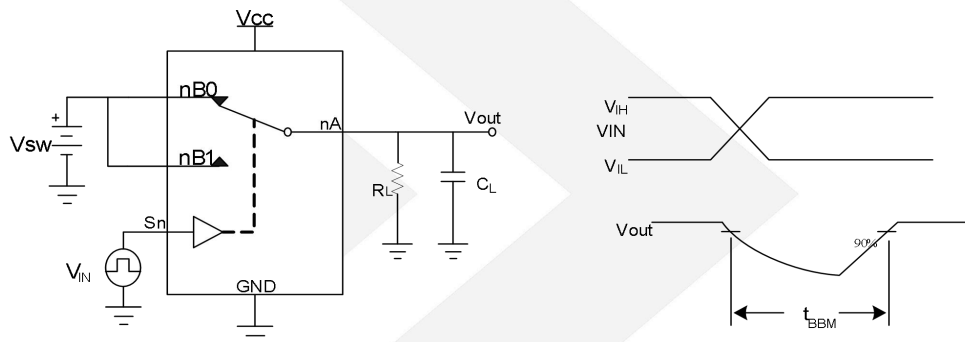


Figure 9. Break-before-make

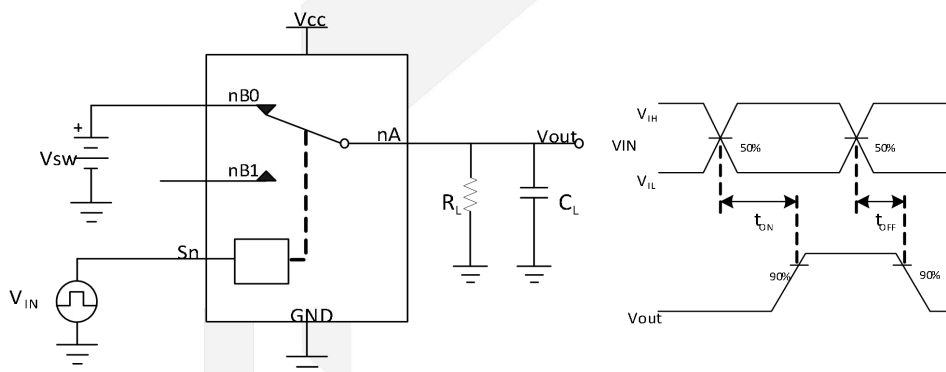
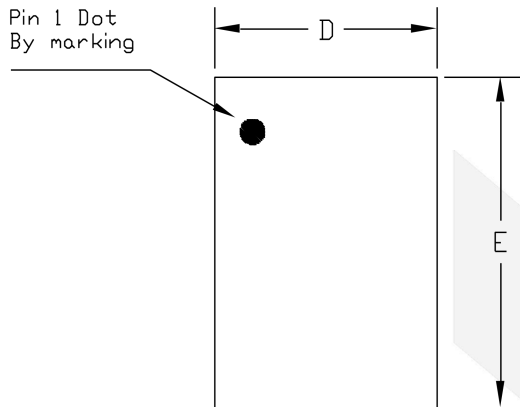
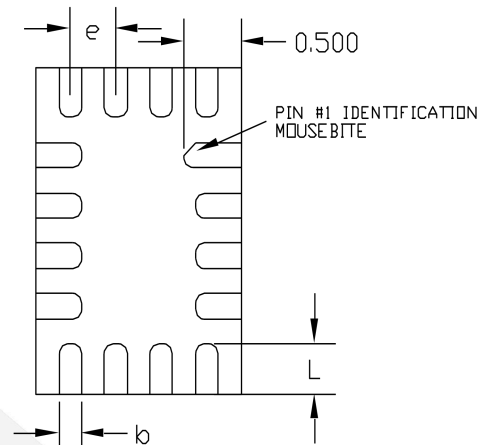


Figure 10. Turn-on/Turn-off

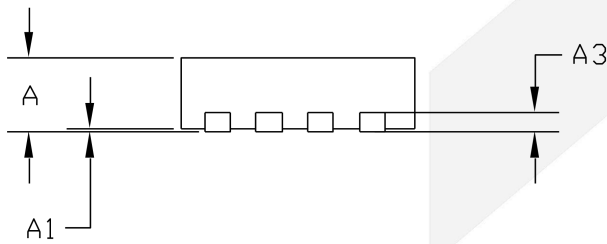
Physical Dimensions: QFN1.8*2.6-16



TOP VIEW



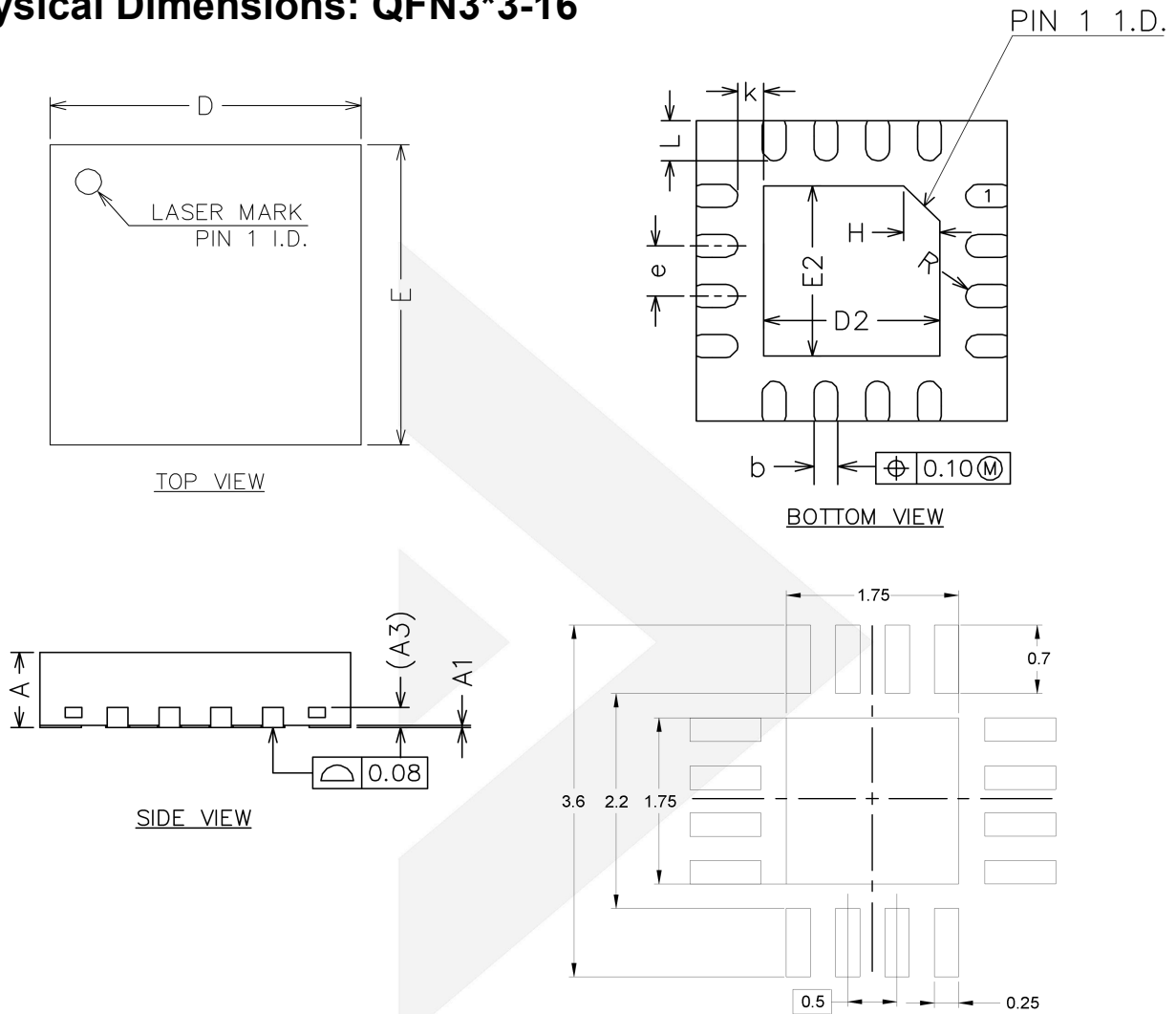
BOTTOM VIEW



SIDE VIEW

Common Dimensions (Units of Measure = Millimeter)			
Symbol	Min	Nom	Max
A	>0.50	0.55	0.60
A1	0.00	-	0.05
A3	0.15 REF		
D	1.75	1.80	1.85
E	2.55	2.60	2.65
L	0.35	0.40	0.45
b	0.15	0.20	0.25
e	0.40 BSC		

Physical Dimensions: QFN3*3-16



Common Dimensions (Units of Measure = Millimeter)			
Symbol	Min	Nom	Max
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
A3	0.20 REF		
b	0.18	0.23	0.28
D	2.90	3.00	3.10
E	2.90	3.00	3.10
D2	1.60	1.70	1.80
E2	1.60	1.70	1.80
e	0.40	0.50	0.60
H	0.35 REF		
K	0.15	0.25	0.35
L	0.30	0.40	0.50
R	0.09	-	-

CONTACT US

Dioo is a professional design and sales corporation for high-quality and performance analog semiconductors. The company focuses on industry markets, such as cell phones, handheld products, laptops, medical equipment, and so on. Dioo's product families include analog signal processing and amplifying, LED drivers, and charger ICs. Go to <http://www.dioo.com> for a complete list of Dioo product families.

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